

**Features:**

- Isolated mounting base 3000V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

**Typical Applications**

- AC/DC Motor drives
- Various rectifiers
- DC supply for PWM inverter

V <sub>DSM</sub> , V <sub>RSM</sub>	V <sub>DRM</sub> , V <sub>RRM</sub>	Type & Outline
2100V	2000V	MT600-20-432F2
2300V	2200V	MT600-22-432F2
2600V	2500V	MT600-25-432F2

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T <sub>J</sub> (°C)	VALUE			UNIT
				Min	Type	Max	
I <sub>T(AV)</sub>	Mean on-state current	180° half sine wave 50Hz Single side cooled, T <sub>c</sub> =85°C	125			600	A
I <sub>T(RMS)</sub>	RMS on-state current					942	A
I <sub>DRM</sub> I <sub>RRM</sub>	Repetitive peak current	at V <sub>DRM</sub> at V <sub>RRM</sub>	125			50	mA
I <sub>TSM</sub>	Surge on-state current	10ms half sine wave V <sub>R</sub> =60%V <sub>RRM</sub>	125			14	kA
I <sup>2</sup> t	I <sup>2</sup> t for fusing coordination					980	10 <sup>3</sup> A <sup>2</sup> s
V <sub>TO</sub>	Threshold voltage	V <sub>DM</sub> =67%V <sub>DRM</sub>	125			0.88	V
r <sub>T</sub>	On-state slope resistance					0.24	mΩ
V <sub>TM</sub>	Peak on-state voltage	I <sub>TM</sub> =1800A		25		1.80	V
dv/dt	Critical rate of rise of off-state voltage	Gate source 1.5A t <sub>r</sub> ≤0.5μs Repetitive	125			800	V/μs
di/dt	Critical rate of rise of on-state current					100	A/μs
I <sub>GT</sub>	Gate trigger current			30		200	mA
V <sub>GT</sub>	Gate trigger voltage	V <sub>A</sub> =12V, I <sub>A</sub> =1A	25	0.8		3.0	V
I <sub>H</sub>	Holding current			10		200	mA
V <sub>GD</sub>	Non-trigger gate voltage	V <sub>DM</sub> =67%V <sub>DRM</sub>				0.2	V
R <sub>th(j-c)</sub>	Thermal resistance Junction to case	Single side cooled per chip				0.054	°C/W
R <sub>th(c-h)</sub>	Thermal resistance case to heat sink	Single side cooled per chip				0.030	°C/W
V <sub>iso</sub>	Isolation voltage	50Hz,R.M.S.,t=1min,I <sub>iso</sub> :1mA(MAX)		3000			V
F <sub>m</sub>	Terminal connection torque (M12)			12.0		14.0	N·m
	Mounting torque (M6)			4.5		6.0	N·m
T <sub>vj</sub>	Junction temperature			-40		125	°C
T <sub>stg</sub>	Stored temperature			-40		125	°C
W <sub>t</sub>	Weight				2700		g
Outline		432F2					

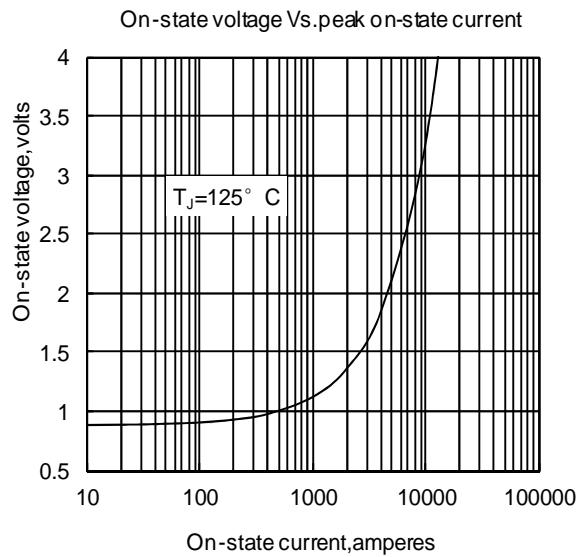


Fig. 1

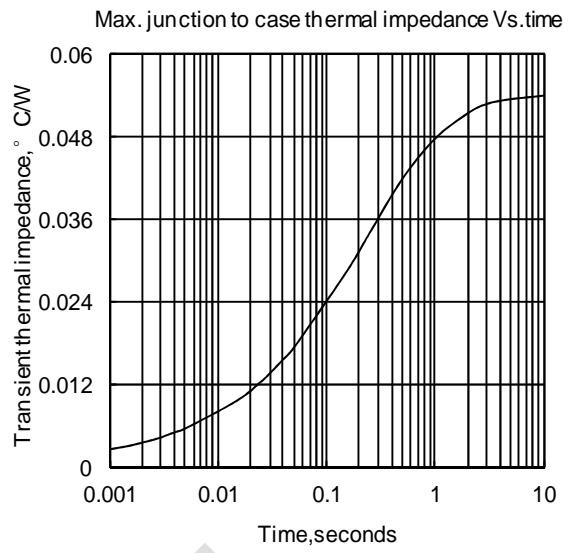


Fig. 2

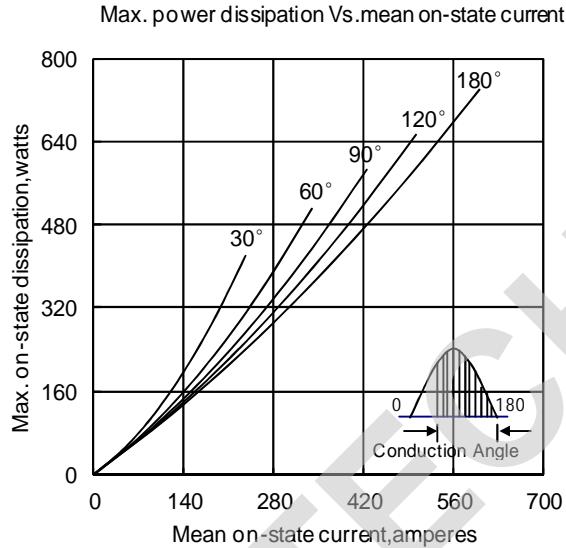


Fig. 3

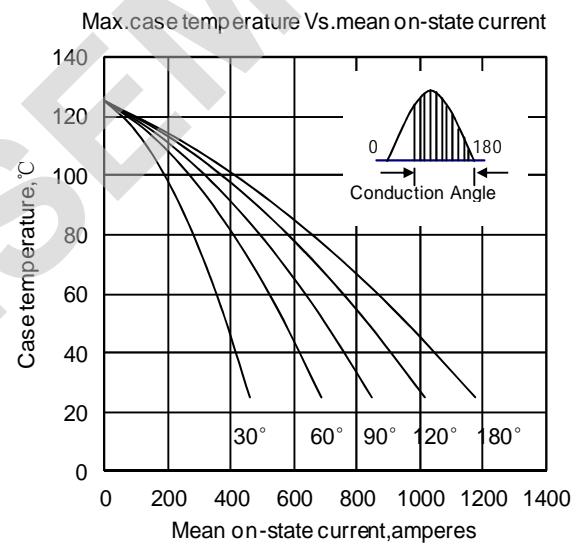


Fig. 4

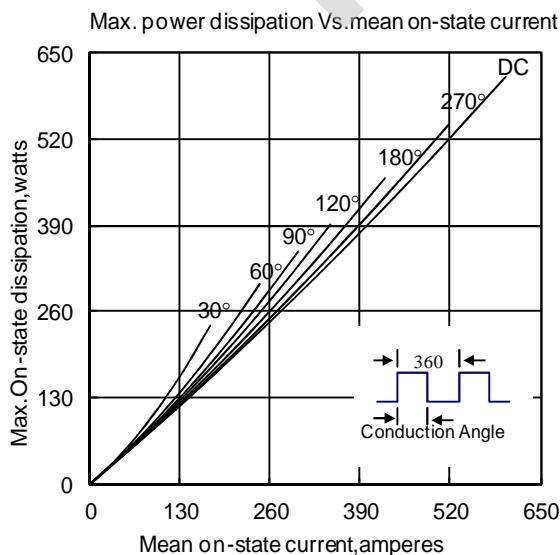


Fig. 5

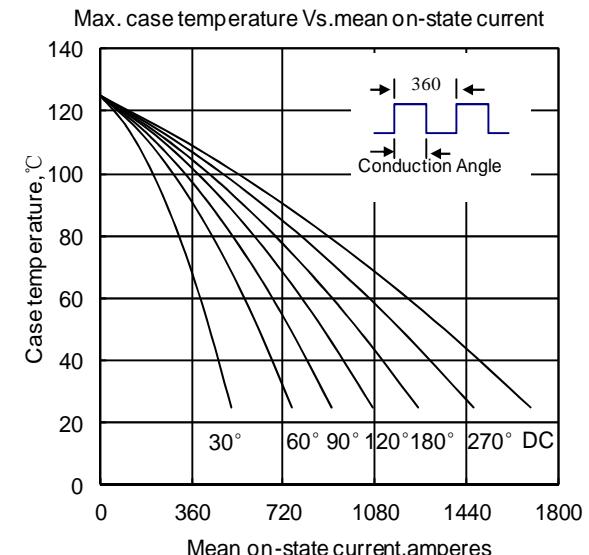


Fig. 6

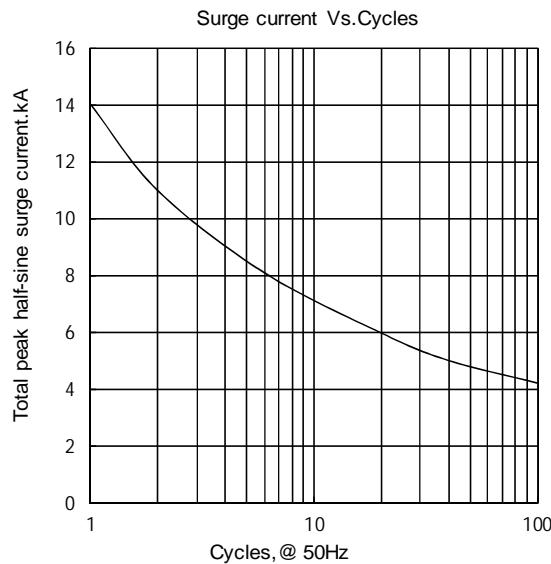


Fig.7

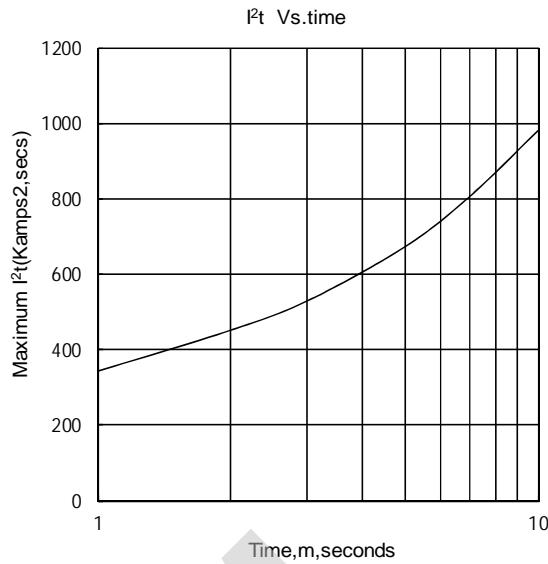


Fig.8

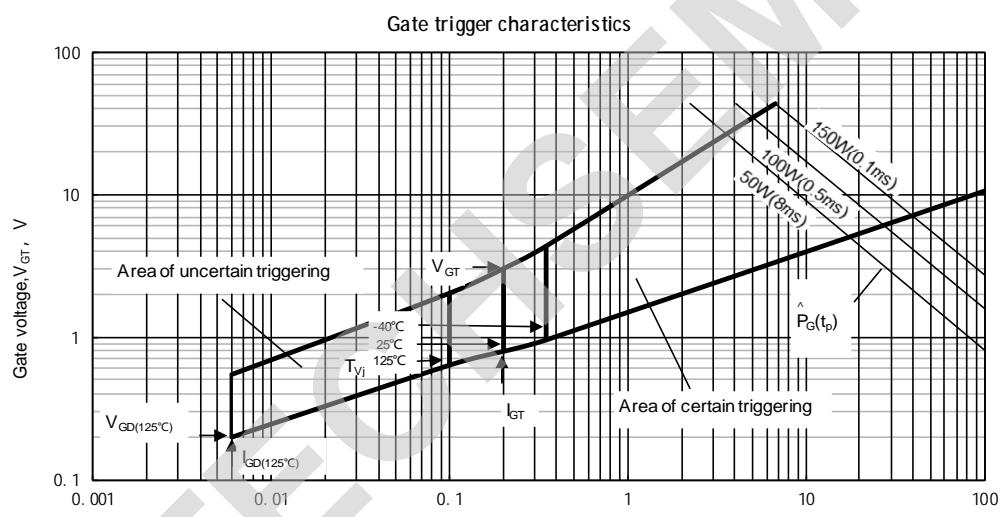
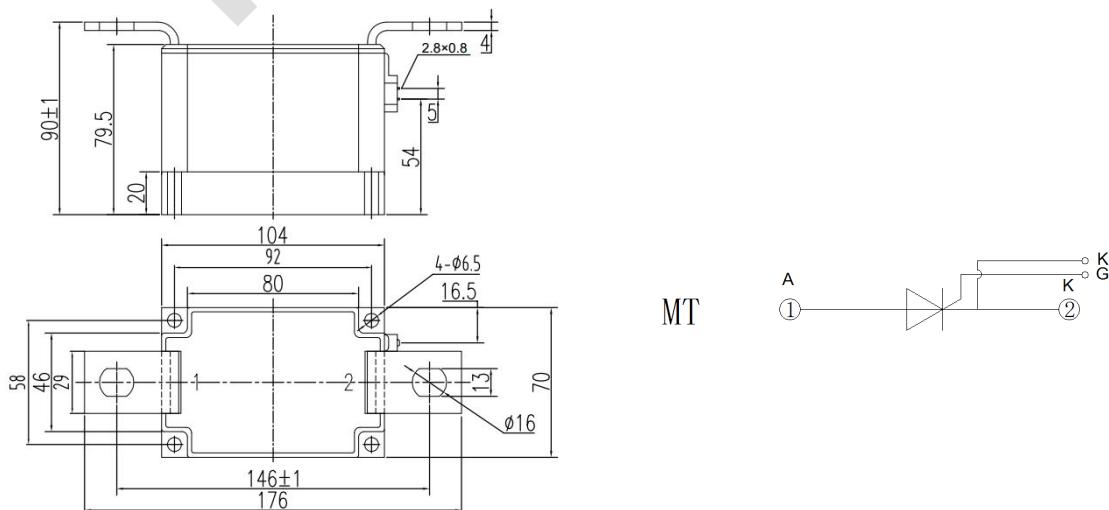


Fig.9

**Outline:****Unmarked dimensional tolerance: ±0.5mm**

TECHSEM reserves the right to change specifications without notice.